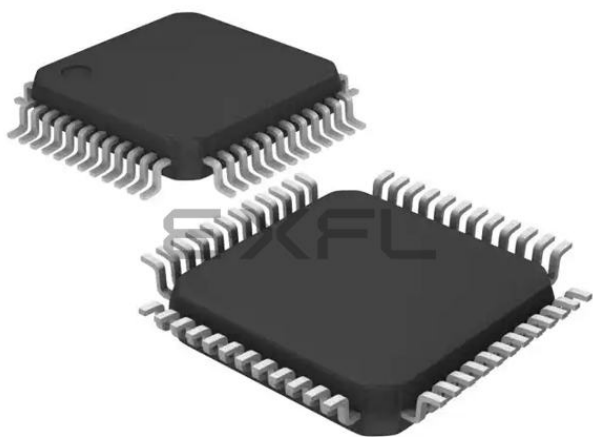




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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100ggdfb-x0

Table 1-1. List of Ordering Part Numbers

(1/12)

Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
20 pins	20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A	R5F1006AASP#V0, R5F1006CASP#V0, R5F1006DASP#V0, R5F1006EASP#V0 R5F1006AASP#X0, R5F1006CASP#X0, R5F1006DASP#X0, R5F1006EASP#X0
			D	R5F1006ADSP#V0, R5F1006CDSP#V0, R5F1006DDSP#V0, R5F1006EDSP#V0 R5F1006ADSP#X0, R5F1006CDSP#X0, R5F1006DDSP#X0, R5F1006EDSP#X0
			G	R5F1006AGSP#V0, R5F1006CGSP#V0, R5F1006DGSP#V0, R5F1006EGSP#V0 R5F1006AGSP#X0, R5F1006CGSP#X0, R5F1006DGSP#X0, R5F1006EGSP#X0
		Not mounted	A	R5F1016AASP#V0, R5F1016CASP#V0, R5F1016DASP#V0, R5F1016EASP#V0 R5F1016AASP#X0, R5F1016CASP#X0, R5F1016DASP#X0, R5F1016EASP#X0
			D	R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0, R5F1016EDSP#V0 R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0, R5F1016EDSP#X0
			G	R5F1016AGSP#V0, R5F1016CGSP#V0, R5F1016DGSP#V0, R5F1016EGSP#V0 R5F1016AGSP#X0, R5F1016CGSP#X0, R5F1016DGSP#X0, R5F1016EGSP#X0
24 pins	24-pin plastic HWQFN (4 × 4mm, 0.5 mm pitch)	Mounted	A	R5F1007AANA#U0, R5F1007CANA#U0, R5F1007DANA#U0, R5F1007EANA#U0 R5F1007AANA#W0, R5F1007CANA#W0, R5F1007DANA#W0, R5F1007EANA#W0
			D	R5F1007ADNA#U0, R5F1007CDNA#U0, R5F1007DDNA#U0, R5F1007EDNA#U0 R5F1007ADNA#W0, R5F1007CDNA#W0, R5F1007DDNA#W0, R5F1007EDNA#W0
			G	R5F1007AGNA#U0, R5F1007CGNA#U0, R5F1007DGNA#U0, R5F1007EGNA#U0 R5F1007AGNA#W0, R5F1007CGNA#W0, R5F1007DGNA#W0, R5F1007EGNA#W0
		Not mounted	A	R5F1017AANA#U0, R5F1017CANA#U0, R5F1017DANA#U0, R5F1017EANA#U0 R5F1017AANA#W0, R5F1017CANA#W0, R5F1017DANA#W0, R5F1017EANA#W0
			D	R5F1017ADNA#U0, R5F1017CDNA#U0, R5F1017DDNA#U0, R5F1017EDNA#U0 R5F1017ADNA#W0, R5F1017CDNA#W0, R5F1017DDNA#W0, R5F1017EDNA#W0
			G	R5F1017AGNA#U0, R5F1017CGNA#U0, R5F1017DGNA#U0, R5F1017EGNA#U0 R5F1017AGNA#W0, R5F1017CGNA#W0, R5F1017DGNA#W0, R5F1017EGNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(8/12)

Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
64 pins	64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)	Mounted	A	R5F100LCAFA#V0, R5F100LDAFA#V0, R5F100LEAFA#V0, R5F100LFAFA#V0, R5F100LGAFA#V0, R5F100LHAFA#V0, R5F100LJFAFA#V0, R5F100LKFAFA#V0, R5F100LLAFA#V0 R5F100LCAFA#X0, R5F100LDAFA#X0, R5F100LEAFA#X0, R5F100LFAFA#X0, R5F100LGAFA#X0, R5F100LHAFA#X0, R5F100LJFAFA#X0, R5F100LKFAFA#X0, R5F100LLAFA#X0 R5F100LCDFA#V0, R5F100LDDFA#V0, R5F100LEDFA#V0, R5F100LFDFA#V0, R5F100LGDAFA#V0, R5F100LHDAFA#V0, R5F100LJDAFA#V0, R5F100LKDAFA#V0, R5F100LLDAFA#V0 R5F100LCDFA#X0, R5F100LDDFA#X0, R5F100LEDFA#X0, R5F100LFDFA#X0, R5F100LGDAFA#X0, R5F100LHDAFA#X0, R5F100LJDAFA#X0, R5F100LKDAFA#X0, R5F100LLDAFA#X0 R5F100LCGFA#V0, R5F100LDGFA#V0, R5F100LEGFA#V0, R5F100LFGFA#V0 R5F100LCGFA#X0, R5F100LDGFA#X0, R5F100LEGFA#X0, R5F100LFGFA#X0 R5F100LGGFA#V0, R5F100LHGFA#V0, R5F100LJGFA#V0 R5F100LGGFA#X0, R5F100LHGFA#X0, R5F100LJGFA#X0
		Not mounted	A	R5F101LCAFA#V0, R5F101LDAFA#V0, R5F101LEAFA#V0, R5F101LFAFA#V0, R5F101LGAFA#V0, R5F101LHAFA#V0, R5F101LJFAFA#V0, R5F101LKFAFA#V0, R5F101LLAFA#V0 R5F101LCAFA#X0, R5F101LDAFA#X0, R5F101LEAFA#X0, R5F101LFAFA#X0, R5F101LGAFA#X0, R5F101LHAFA#X0, R5F101LJFAFA#X0, R5F101LKFAFA#X0, R5F101LLAFA#X0 R5F101LCDFA#V0, R5F101LDDFA#V0, R5F101LEDFA#V0, R5F101LFDFA#V0, R5F101LGDAFA#V0, R5F101LHDAFA#V0, R5F101LJDAFA#V0, R5F101LKDAFA#V0, R5F101LLDAFA#V0 R5F101LCDFA#X0, R5F101LDDFA#X0, R5F101LEDFA#X0, R5F101LFDFA#X0, R5F101LGDAFA#X0, R5F101LHDAFA#X0, R5F101LJDAFA#X0, R5F101LKDAFA#X0, R5F101LLDAFA#X0

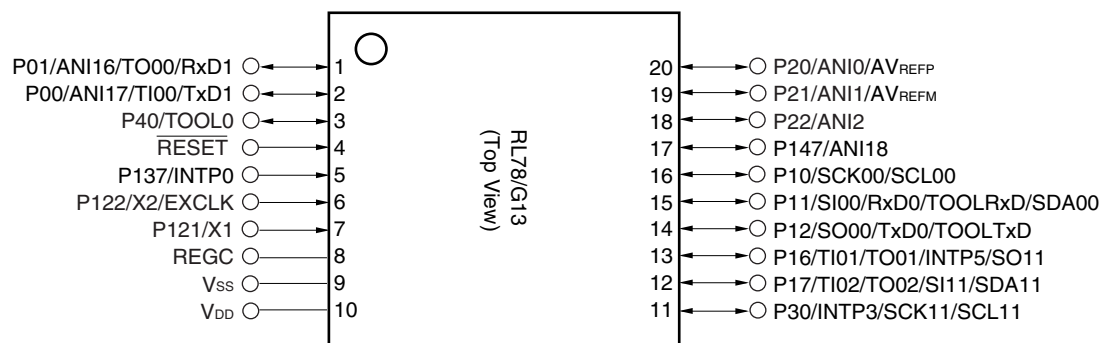
Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

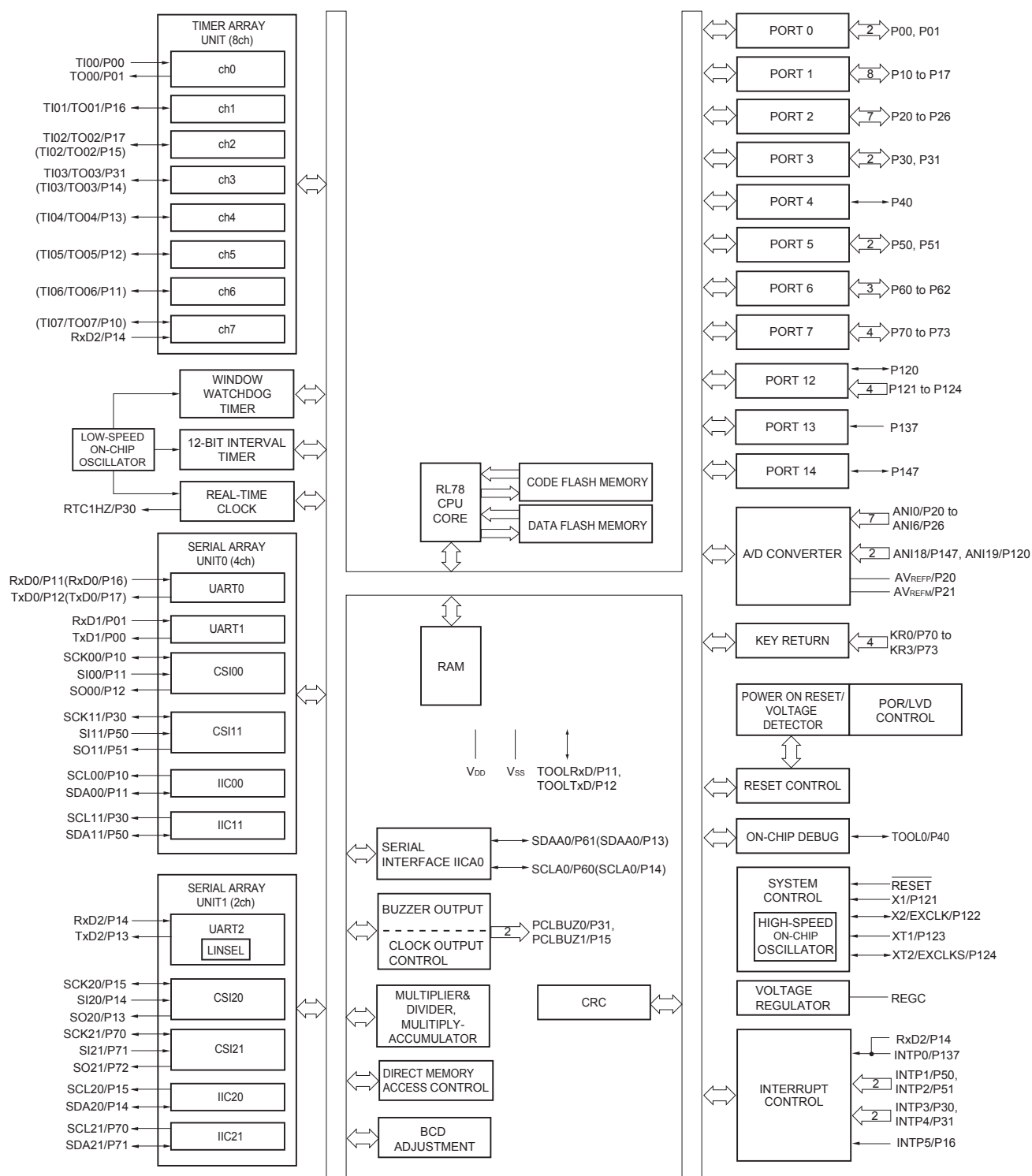
- 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see 1.4 Pin Identification.

1.5.7 40-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EV _{SS0} , EV _{SS1}	EV _{SS0} = EV _{SS1}	-0.5 to +0.3	V
REGC pin input voltage	V _{IREGC}	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	V _{I1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	V _{I3}	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Output voltage	V _{O1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Analog input voltage	V _{AI1}	ANI16 to ANI26	-0.3 to EV _{DD0} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V
	V _{AI2}	ANI0 to ANI14	-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V

Notes 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. AV_{REF}(+) : + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
8. Current flowing only during data flash rewrite.
9. Current flowing only during self programming.
10. For shift time to the SNOOZE mode, see **18.3.3 SNOOZE mode**.

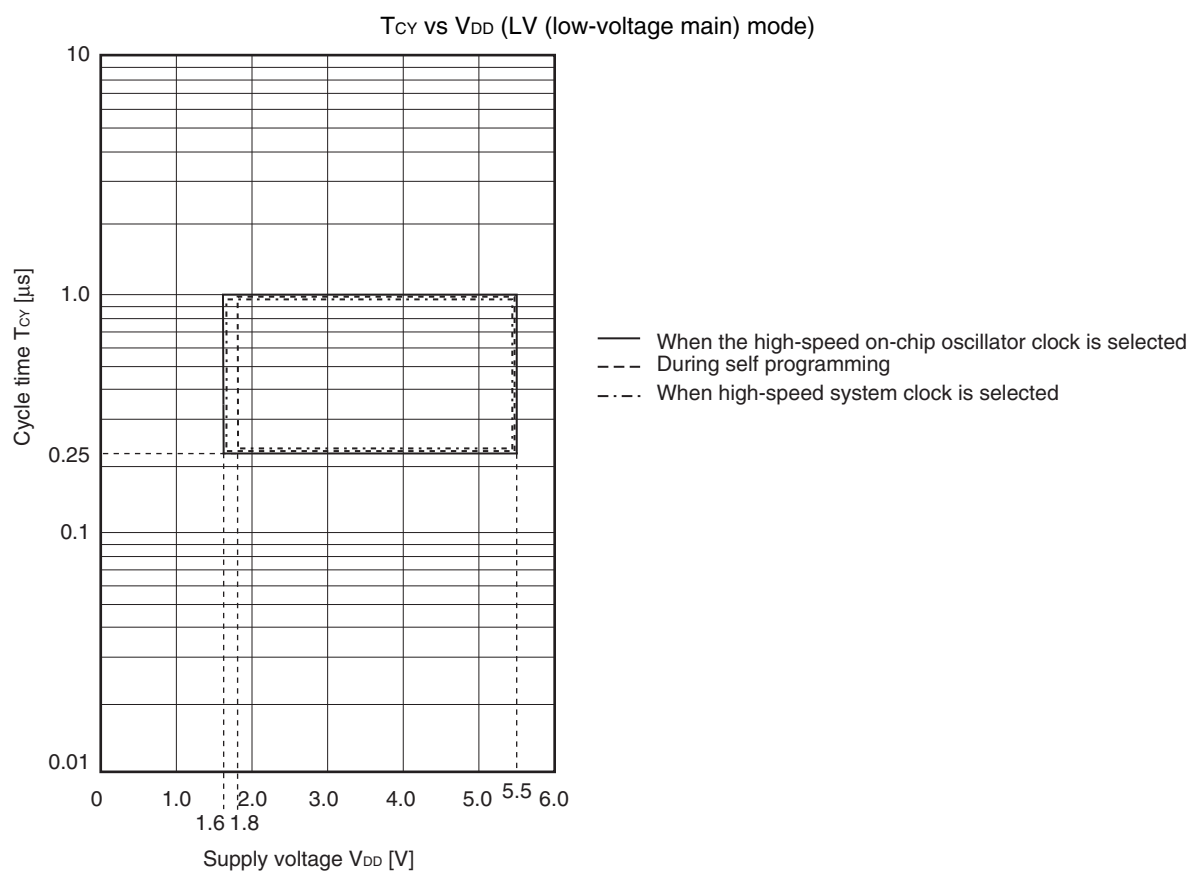
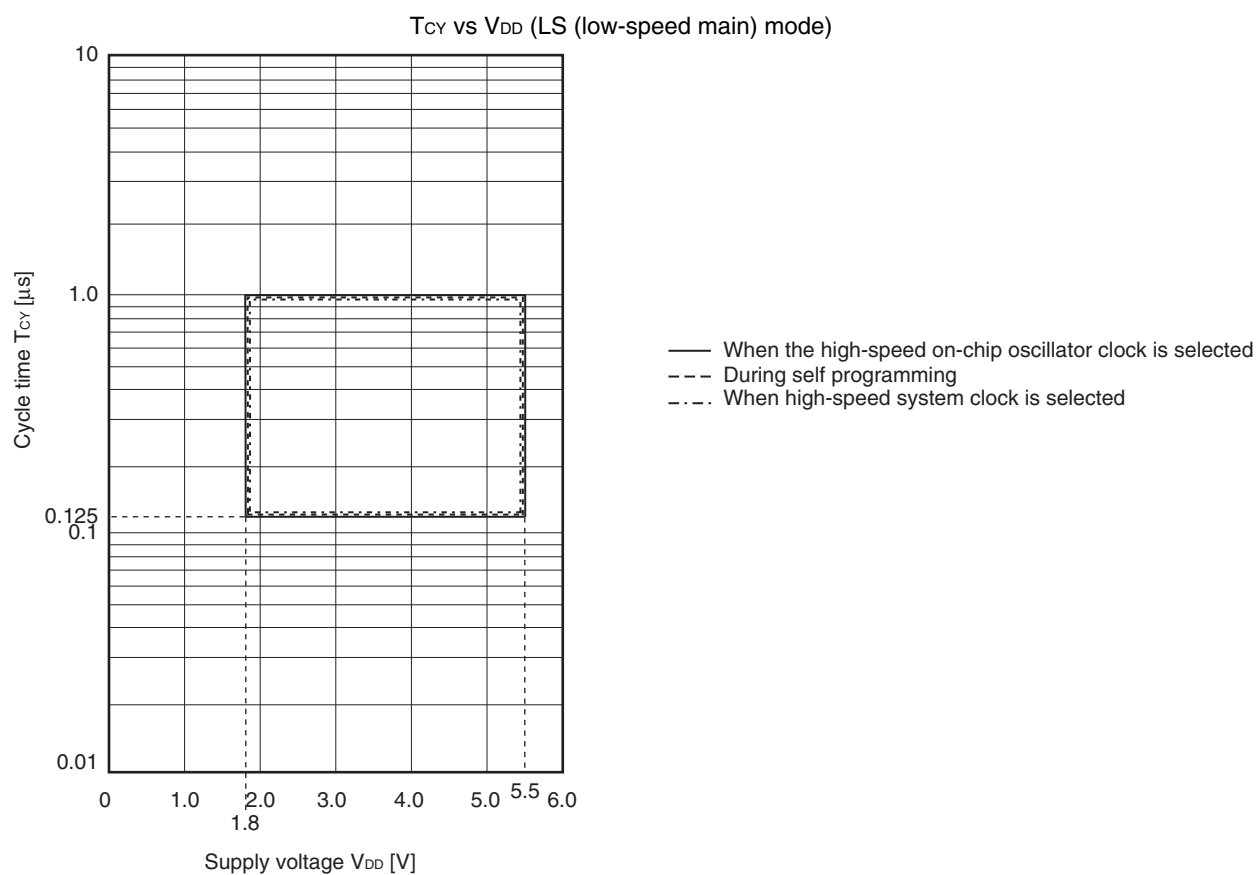
- Remarks**
1. f_{IL} : Low-speed on-chip oscillator clock frequency
 2. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 3. f_{CLK} : CPU/peripheral hardware clock frequency
 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

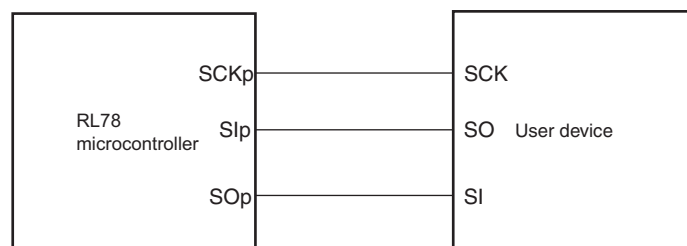
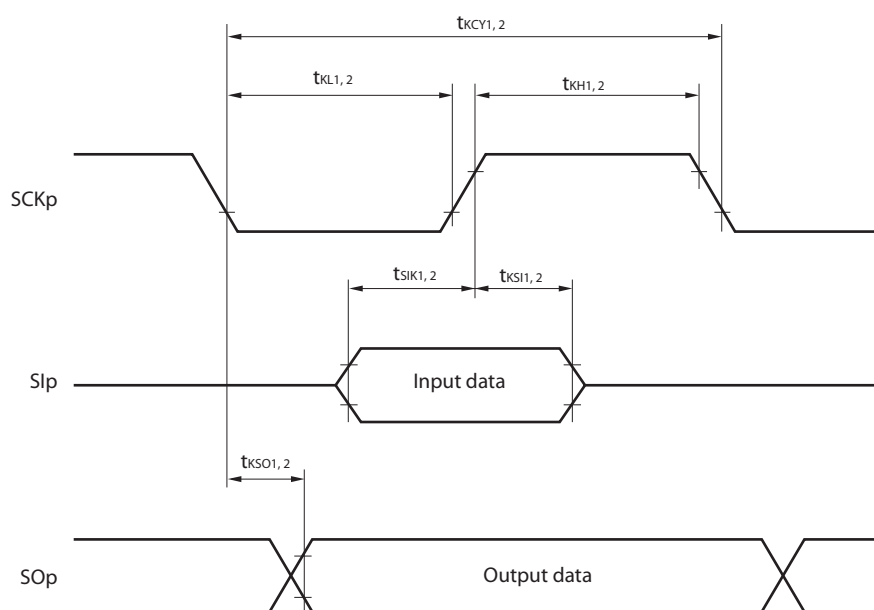
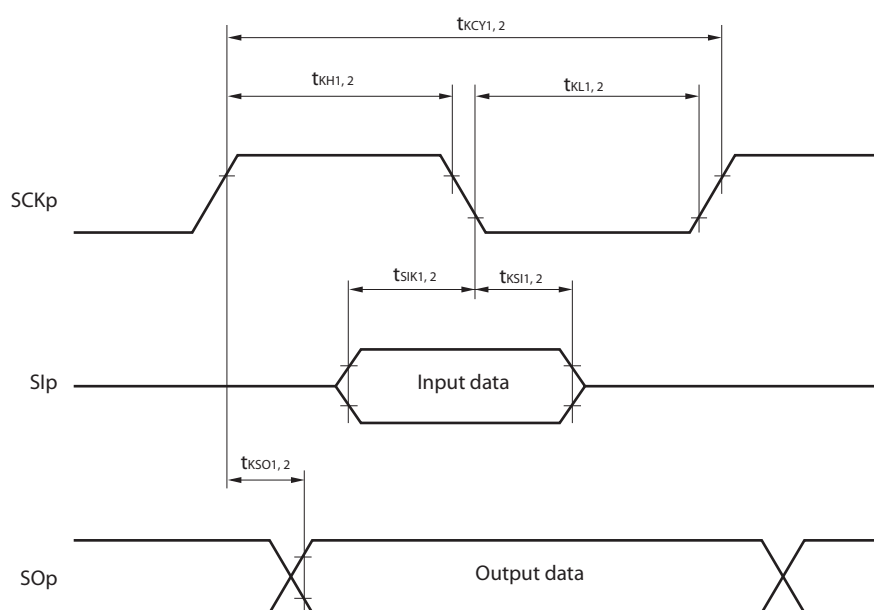
2.4 AC Characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

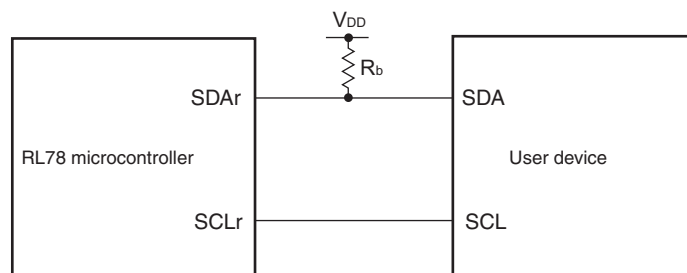
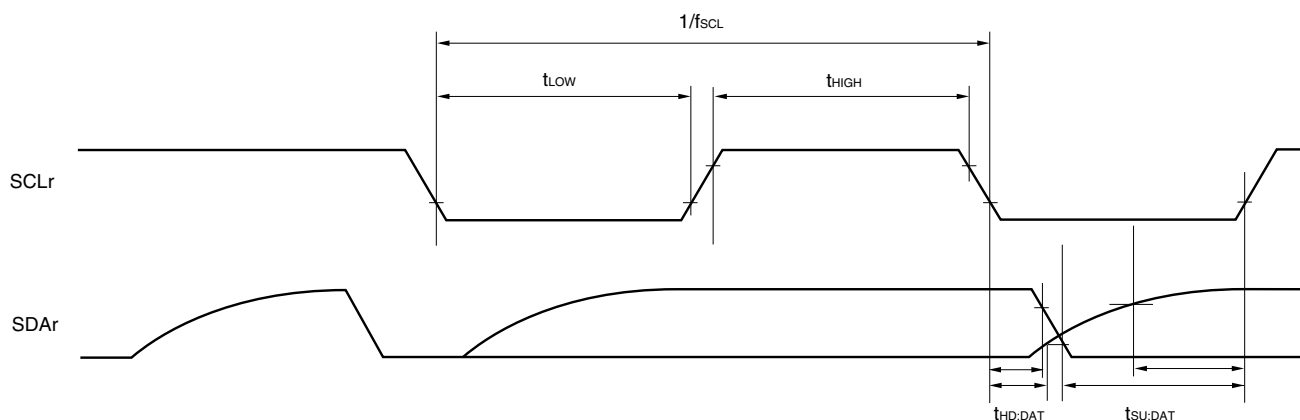
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{CY}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
		Subsystem clock (f _{SUB}) operation		1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3 μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V		1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V		1.0		4.0	MHz
	f _{EXS}			32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V		24			ns
		2.4 V ≤ V _{DD} < 2.7 V		30			ns
		1.8 V ≤ V _{DD} < 2.4 V		60			ns
		1.6 V ≤ V _{DD} < 1.8 V		120			ns
	t _{EXHS} , t _{EXLS}			13.7			μs
Ti00 to Ti07, Ti10 to Ti17 input high-level width, low-level width	t _{TIH} , t _{TIL}			1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.6 V ≤ EV _{DD0} ≤ 5.5 V		2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0	1.6 V ≤ V _{DD} ≤ 5.5 V	1			μs
		INTP1 to INTP11	1.6 V ≤ EV _{DD0} ≤ 5.5 V	1			μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7	1.8 V ≤ EV _{DD0} ≤ 5.5 V	250			ns
			1.6 V ≤ EV _{DD0} < 1.8 V	1			μs
RESET low-level width	t _{RSL}			10			μs

(Note and Remark are listed on the next page.)



CSI mode connection diagram (during communication at same potential)**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)****CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**

- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

Simplified I²C mode connection diagram (during communication at same potential)**Simplified I²C mode serial transfer timing (during communication at same potential)**

- Remarks**
- $R_b[\Omega]$: Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance
 - r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14),
h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
 - f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode(T_A = -40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V _{LVD0}	Power supply rise time	3.98	4.06	4.14	V
			Power supply fall time	3.90	3.98	4.06	V
		V _{LVD1}	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		V _{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V _{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V _{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V _{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V _{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V _{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V _{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V _{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V _{LVD10}	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		V _{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V _{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V _{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width		t _{LW}		300			μs
Detection delay time						300	μs

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD0} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = V_{SS0} = 0\text{ V}$) (2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.54	2.90	mA	
					V _{DD} = 3.0 V		0.54	2.90	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	2.30	mA	
					V _{DD} = 3.0 V		0.44	2.30	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.40	1.70	mA	
					V _{DD} = 3.0 V		0.40	1.70	mA	
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.28	1.90	mA	
					Resonator connection		0.45	2.00	mA	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.28	1.90	mA	
					Resonator connection		0.45	2.00	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.19	1.02	mA	
					Resonator connection		0.26	1.10	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.19	1.02	mA	
					Resonator connection		0.26	1.10	mA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.25	0.57	μA	
					Resonator connection		0.44	0.76	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.30	0.57	μA	
					Resonator connection		0.49	0.76	μA	
		f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C		Square wave input		0.37	1.17	μA		
				Resonator connection		0.56	1.36	μA		
		f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C		Square wave input		0.53	1.97	μA		
				Resonator connection		0.72	2.16	μA		
		f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C		Square wave input		0.82	3.37	μA		
				Resonator connection		1.01	3.56	μA		
		f _{SUB} = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		3.01	15.37	μA			
			Resonator connection		3.20	15.56	μA			
	I _{DD3} ^{Note 6}	STOP mode ^{Note 8}	T _A = −40°C					0.18	0.50	μA
			T _A = +25°C					0.23	0.50	μA
			T _A = +50°C					0.30	1.10	μA
			T _A = +70°C					0.46	1.90	μA
			T _A = +85°C					0.75	3.30	μA
			T _A = +105°C					2.94	15.30	μA

(Notes and Remarks are listed on the next page.)

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	$f_{\text{IH}} = 32\text{ MHz}$ Note 3	Basic operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		2.3		mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		2.3		mA
					Normal operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		5.2	9.2	mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		5.2	9.2	mA
				$f_{\text{IH}} = 24\text{ MHz}$ Note 3	Normal operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		4.1	7.0	mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		4.1	7.0	mA
				$f_{\text{IH}} = 16\text{ MHz}$ Note 3	Normal operation	$\text{V}_{\text{DD}} = 5.0\text{ V}$		3.0	5.0	mA
						$\text{V}_{\text{DD}} = 3.0\text{ V}$		3.0	5.0	mA
			HS (high-speed main) mode Note 5	$f_{\text{MX}} = 20\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 5.0\text{ V}$	Normal operation	Square wave input		3.4	5.9	mA
						Resonator connection		3.6	6.0	mA
				$f_{\text{MX}} = 20\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 3.0\text{ V}$	Normal operation	Square wave input		3.4	5.9	mA
						Resonator connection		3.6	6.0	mA
				$f_{\text{MX}} = 10\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 5.0\text{ V}$	Normal operation	Square wave input		2.1	3.5	mA
						Resonator connection		2.1	3.5	mA
				$f_{\text{MX}} = 10\text{ MHz}$ Note 2, $\text{V}_{\text{DD}} = 3.0\text{ V}$	Normal operation	Square wave input		2.1	3.5	mA
						Resonator connection		2.1	3.5	mA
		Subsystem clock operation		$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.8	5.9	μA
						Resonator connection		4.9	6.0	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		4.9	5.9	μA
						Resonator connection		5.0	6.0	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.0	7.6	μA
						Resonator connection		5.1	7.7	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.2	9.3	μA
						Resonator connection		5.3	9.4	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		5.7	13.3	μA
						Resonator connection		5.8	13.4	μA
				$f_{\text{SUB}} = 32.768\text{ kHz}$ Note 4 $T_A = +105^\circ\text{C}$	Normal operation	Square wave input		10.0	46.0	μA
						Resonator connection		10.0	46.0	μA

(Notes and Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{\text{KCY1}} \geq 4/f_{\text{CLK}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	600		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	1000		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	2300		ns
SCKp high-level width	t_{KH1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 150$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 340$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 916$		ns
SCKp low-level width	t_{KL1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 24$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 36$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 100$		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp $\uparrow$) ^{Note}	t_{SIK1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	162		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	354		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	958		ns
Slp hold time (from SCKp $\uparrow$) ^{Note}	t_{KSI1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	38		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	38		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	38		ns
Delay time from SCKp $\downarrow$ to SOp output ^{Note}	t_{KSO1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		200	ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		390	ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Data setup time (reception)	$t_{\text{SU:DAT}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$1/f_{\text{MCK}} + 570$ Note 2		ns
Data hold time (transmission)	$t_{\text{HD:DAT}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	0	1420	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	1420	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	0	1215	ns

Notes 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.2. Set the f_{MCK} value to keep the hold time of $\text{SCLr} = \text{"L"}$ and $\text{SCLr} = \text{"H"}$.

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

3.8 Flash Memory Programming Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	1		32	MHz
Number of code flash rewrites Notes 1,2,3	C _{enwr}	Retained for 20 years $T_A = 85^\circ\text{C}$ Note 4	1,000			Times
Number of data flash rewrites Notes 1,2,3		Retained for 1 years $T_A = 25^\circ\text{C}$		1,000,000		
		Retained for 5 years $T_A = 85^\circ\text{C}$ Note 4	100,000			
		Retained for 20 years $T_A = 85^\circ\text{C}$ Note 4	10,000			

- Notes**
- 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 2. When using flash memory programmer and Renesas Electronics self programming library.
 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 4. This temperature is the average value at which data are retained.

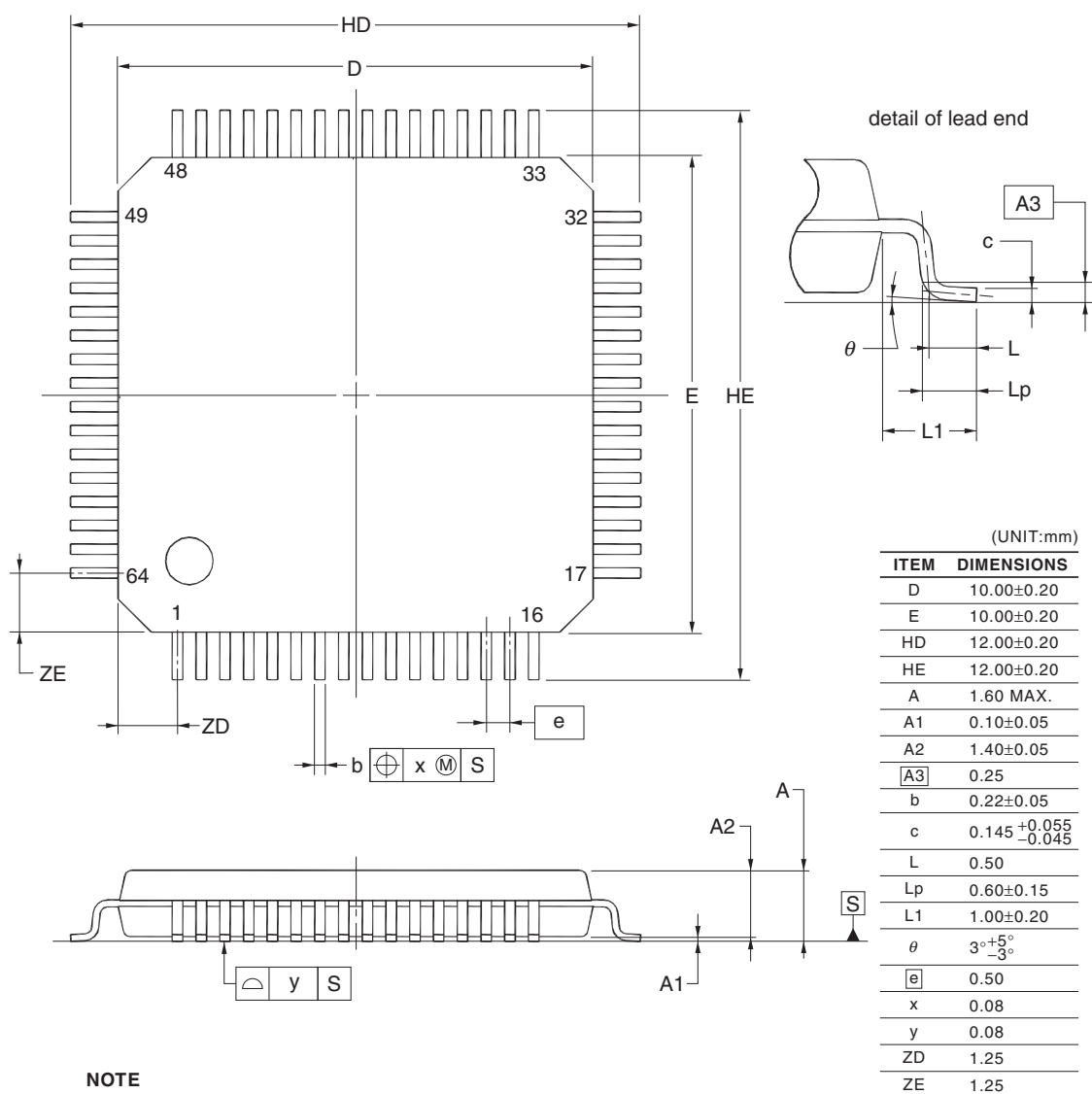
3.9 Dedicated Flash Memory Programmer Communication (UART)

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD0} = V_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = V_{SS0} = V_{SS1} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

R5F100LCAFB, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB,
 R5F100LKAFB, R5F100LLAFB
 R5F101LCAFB, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB,
 R5F101LJAFB, R5F101LKAFB, R5F101LLAFB
 R5F100LCDFB, R5F100LDDFB, R5F100LEDFB, R5F100LDFB, R5F100LGDFB, R5F100LHDFB, R5F100LJDFB,
 R5F100LKDFB, R5F100LLDFB
 R5F101LCDFB, R5F101LDDFB, R5F101LEDFB, R5F101LDFB, R5F101LGDFB, R5F101LHDFB,
 R5F101LJDFB, R5F101LKDFB, R5F101LLDFB
 R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB,
 R5F100LJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35



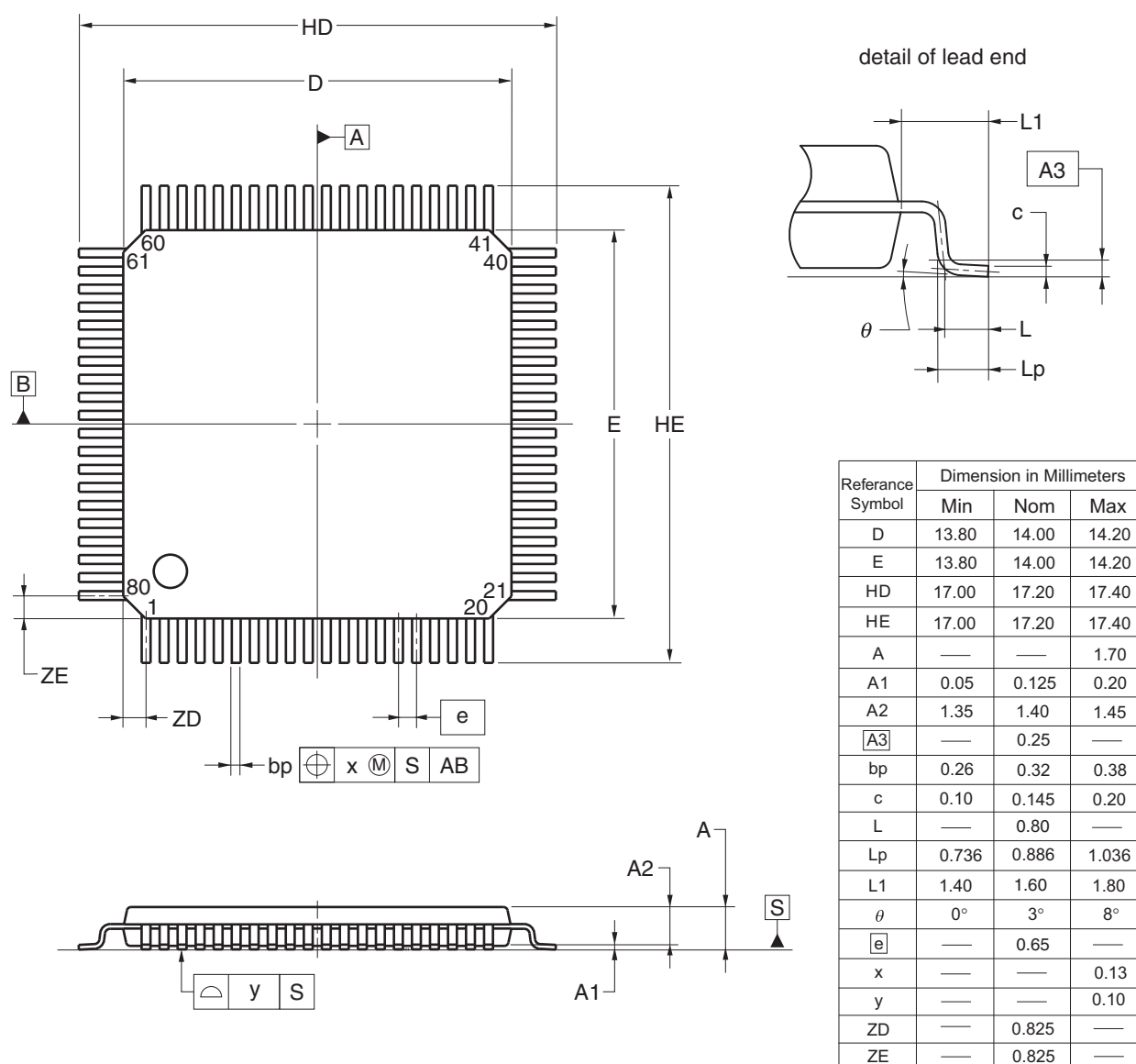
NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

4.12 80-pin Products

R5F100MFAFA, R5F100MGFAFA, R5F100MHAFA, R5F100MJFAFA, R5F100MKAFA, R5F100MLAFA
 R5F101MFAFA, R5F101MGFAFA, R5F101MHAFA, R5F101MJFAFA, R5F101MKAFA, R5F101MLAFA
 R5F100MFDFA, R5F100MGDFA, R5F100MHDFA, R5F100MJDFA, R5F100MKDFA, R5F100MLDFA
 R5F101MFDFA, R5F101MGDFA, R5F101MHDFA, R5F101MJDFA, R5F101MKDFA, R5F101MLDFA
 R5F100MFGFA, R5F100MGGFA, R5F100MHGFA, R5F100MJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



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Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)
		164, 165	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)
		166	Modification of table in 3.5.2 Serial interface IICA
		166	Modification of IICA serial transfer timing
		167	Addition of table in 3.6.1 A/D converter characteristics
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)
		169	Modification of description in 3.6.1 (2)
		170	Modification of description and note 3 in 3.6.1 (3)
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)
		172	Modification of table and note in 3.6.3 POR circuit characteristics
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage rising slope characteristics
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes
3.10	Nov 15, 2013	123	Caution 4 added.
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.
3.30	Mar 31, 2016		Modification of the position of the index mark in 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products
			Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]
			ACK corrected to ACK
			ACK corrected to ACK

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